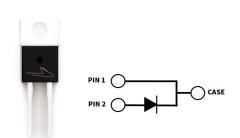


### 3rd Generation 600 V, 4 A Silicon Carbide Schottky

### **Description**

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.







Wolfspeed, Inc. is in the process of rebranding its products and related materials pursuant to the entity name change from Cree, Inc. to Wolfspeed, Inc. During this transition period, products received may be marked with either the Cree name and/or logo or the Wolfspeed name and/or logo.

Part Number	Package	Marking	
C3D04060A	TO-220-2	C3D04060	

#### **Features**

- Low Forward Voltage (V<sub>F</sub>) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior

### **Applications**

- Industrial Switched Mode Power Supplies
- Uninterruptible & AUX Power Supplies
- Boost for PFC & DC-DC Stages
- Solar Inverters

# **Key Parameters** (T<sub>c</sub> = 25°C Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Conditions	Notes
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	600	V		
DC Blocking Voltage	V <sub>DC</sub>	600	V		
		13.5		T <sub>c</sub> = 25 °C	
Continuous Forward Current	I <sub>F</sub>	6		T <sub>c</sub> = 135 °C	Fig. 3
		4		T <sub>c</sub> = 155 °C	
Repetitive Peak Forward Surge		17		T <sub>c</sub> = 25 °C, t <sub>p</sub> = 10 ms, Half Sine Wave	
Current	FRM	12	Α	$T_c = 110 ^{\circ}\text{C}$ , $t_p = 10 \text{ms}$ , Half Sine Wave	
Non-Repetitive Forward Surge		30.5		T <sub>c</sub> = 25 °C, t <sub>p</sub> = 10 ms, Half Sine Wave	F: 0
Current	FSM	20		$T_c = 110 ^{\circ}\text{C}, t_p = 10 \text{ms},  \text{Half Sine Wave}$	Fig. 8
Non-Repetitive Peak Forward		220		$T_c = 25 ^{\circ}\text{C}, t_D = 10 \mu\text{s}, \text{Pulse}$	
Surge Current	F,Max	160		$T_{c} = 110 {}^{\circ}\text{C}, t_{p} = 10 \mu\text{s}, \text{Pulse}$	
	_	52		T <sub>c</sub> = 25 °C	
Power Dissipation	P <sub>tot</sub>	22.5	W	T <sub>C</sub> = 110 °C	Fig. 4

### **Electrical Characteristics**

Parameter	Symbol	Тур.	Max.	Unit	Test Conditions	Notes
Famous ad Malda as	V	1.4	1.7		I <sub>F</sub> = 4 A, T <sub>j</sub> = 25 °C	F:_ 1
Forward Voltage	V <sub>F</sub>	1.7	2.4	V	I <sub>F</sub> = 4 A, T <sub>j</sub> = 175 °C	Fig. 1
Davis and Comment		5	25		$V_R = 600 \text{ V}, T_j = 25 \text{ °C}$	F:- 2
Reverse Current	I <sub>R</sub>	10	100	μΑ	$V_R = 600 \text{ V}, T_j = 175 \text{ °C}$	Fig. 2
Total Capacitive Charge	Q <sub>c</sub>	10		nC	$V_R = 400 \text{ V}, T_j = 25 \text{ °C}$	Fig. 5
		231			$V_R = 0 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	
Total Capacitance	С	18.5		pF	$V_R = 200 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	Fig. 6
		15			$V_R = 400 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	
Capacitance Stored Energy	E <sub>c</sub>	1.4		μJ	V <sub>R</sub> = 400 V	Fig. 7

#### Notes:

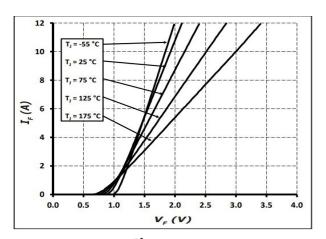
SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

### **Thermal & Mechanical Characteristics**

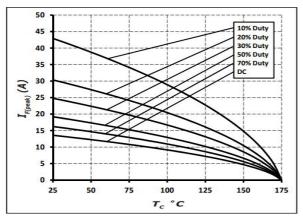
Parameter	Symbol	Value	Unit	Notes
Thermal Resistance, Junction to Case (Typical)	R <sub>0, JC (TYP)</sub>	2.9	°C/W	
Junction Temperature	T <sub>j</sub>	-55 to +175		
Case & Storage Temperature	T <sub>c</sub>	-55 to +175	°C	
T0 000 M		1	Nm	M3 Screw
TO-220 Mounting Torque	-	8.8	lbf-in	6-32 Screw

Parameter	Symbol	Notes
Human Body Model	НВМ	Class 3B (≥ 8000V)
Charge Device Model	CDM	Class C3 (≥1000V)

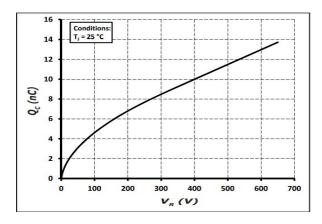
### **Typical Performance**



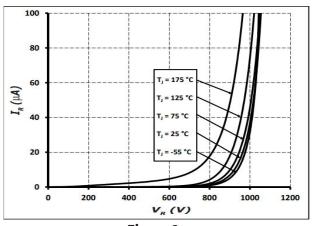
**Figure 1** Forward Characteristics



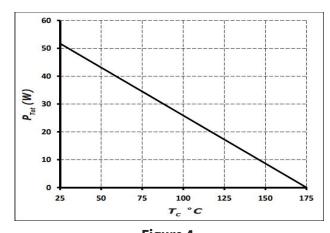
**Figure 3**Current Derating



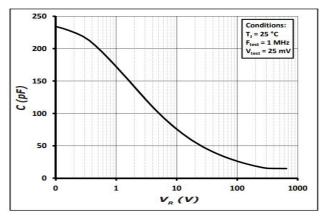
**Figure 5**Total Capacitance Charge vs. Reverse Voltage



**Figure 2**Reverse Characteristics

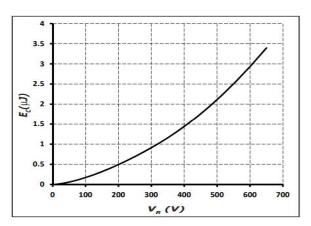


**Figure 4**Power Derating

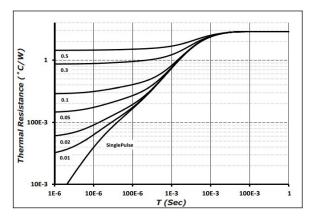


**Figure 6**Capacitance vs. Reverse Voltage

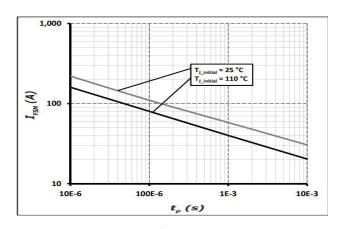
## **Typical Performance**



**Figure 7**Capacitance Stored Energy



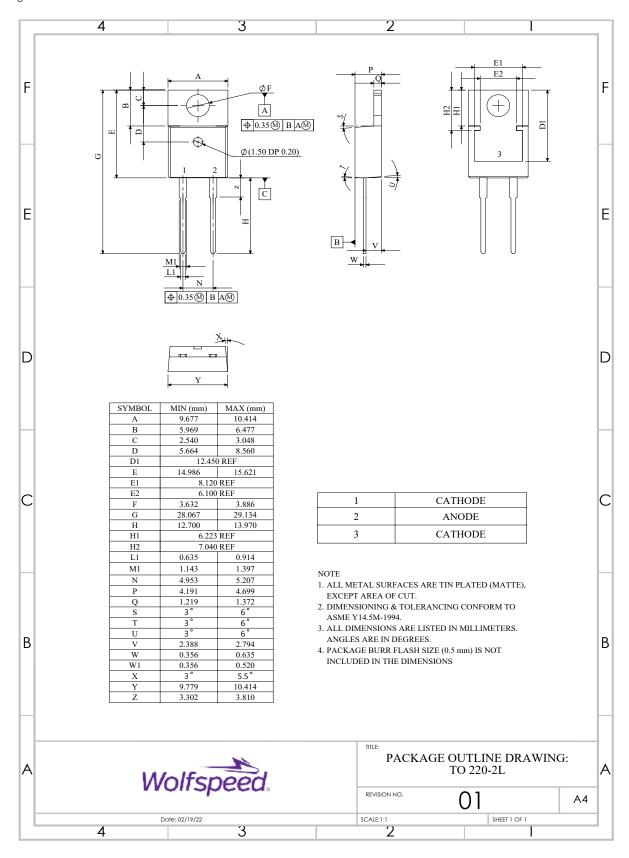
**Figure 9**Transient Thermal Impedance



**Figure 8**Non-Repetitive Peak Forward Surge Current vs. Pulse Duraion

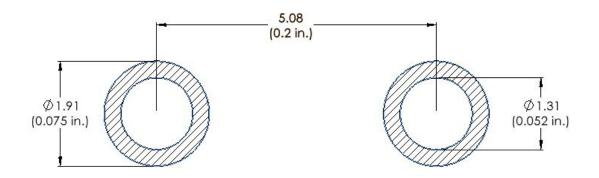
### **Package Dimensions & Pin-Out**

Package: TO-220-2



### **Recommended Solder Pad Layout**

Primary dimensions shown in mm.



# **Product Ordering Information**

Order Number	Packing Type
C3D04060A	Tube

# **Revision History**

Document Version	Date of Release	Description of Changes
1	August-2016	Initial Release
10	March-2023	Update Package Drawing Update Landing Pad
11	July-2023	Updated Test Conditions of I <sub>F</sub> and P <sub>TOT</sub> Added package marking statement
12	August-2023	Updated Package Image Added Wolfspeed Branding Statement Renamed Table on Page 1 Re-added ESD Table

### Notes & Disclaimer

This document and the information contained herein are subject to change without notice. Any such change shall be evidenced by the publication of an updated version of this document by Wolfspeed. No communication from any employee or agent of Wolfspeed or any third party shall effect an amendment or modification of this document. No responsibility is assumed by Wolfspeed for any infringement of patents or other rights of third parties which may result from use of the information contained herein. No license is granted by implication or otherwise under any patent or patent rights of Wolfspeed.

Notwithstanding any application-specific information, guidance, assistance, or support that Wolfspeed may provide, the buyer of this product is solely responsible for determining the suitability of this product for the buyer's purposes, including without limitation for use in the applications identified in the next bullet point, and for the compliance of the buyers' products, including those that incorporate this product, with all applicable legal, regulatory, and safety-related requirements.

This product has not been designed or tested for use in, and is not intended for use in, applications in which failure of the product would reasonably be expected to cause death, personal injury, or property damage, including but not limited to equipment implanted into the human body, life-support machines, cardiac defibrillators, and similar emergency medical equipment, aircraft navigation, communication, and control systems, aircraft power and propulsion systems, air traffic control systems, and equipment used in the planning, construction, maintenance, or operation of nuclear facilities.

### **RoHS Compliance**

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Wolfspeed representative or from the Product Documentation sections of www.wolfspeed. com.

#### **REACh Compliance**

REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact your Wolfspeed representative to ensure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

#### **Contact info:**

4600 Silicon Drive Durham, NC 27703 USA Tel: +1.919.313.5300 www.wolfspeed.com/power

© 2023 Wolfspeed, Inc. All rights reserved. Wolfspeed® and the Wolfstreak logo are registered trademarks and the Wolfspeed logo is a trademark of Wolfspeed, Inc. PATENT: https://www.wolfspeed.com/legal/patents

The information in this document is subject to change without notice.